

# Pressure dependence of the optical phonons and transv

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Citation Report

#	ARTICLE	IF	CITATIONS
1	Dependence on volume of the phonon frequencies and the ir effective charges of several III-V semiconductors. Physical Review B, 1983, 28, 4579-4584.	3.2	330
2	Diamond anvil cell and high-pressure physical investigations. Reviews of Modern Physics, 1983, 55, 65-108.	45.6	1,171
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8	Effects of Strains on the Dynamic Effective Charge of III-V Semiconductors. Physica Status Solidi (B): Basic Research, 1985, 129, 101-116.	1.5	26
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